

IN THE CLAIMS:

Please cancel Claims 10 and 13 without prejudice to or disclaimer of the subject matter presented therein. Please amend Claims 1, 8, and 9, and add new Claims 14 to 16, as shown below.

1. (Currently Amended) A method of manufacturing a thin-film semiconductor device, comprising:

- a step of preparing a member having (a) a semiconductor film with a semiconductor element and/or semiconductor integrated circuit and (b) a separation layer on which the semiconductor film is disposed;
- ~~a bonding step of bonding the member to a support member via an adhesive;~~
- a separation step of separating the member at the separation layer by ~~applying a pressure of a fluid to the side surface of the separation layer;~~ and
- a chip forming step of, ~~after the separation step,~~ dividing the semiconductor film into chips; and
- a removing step of, after the separation step, removing a portion of the separation layer remaining on the semiconductor film.

2. (Original) The method according to claim 1, wherein the member is obtained by forming a porous layer on a surface of a semiconductor substrate, forming the semiconductor film on a surface of the porous layer, and then forming the semiconductor element and/or semiconductor integrated circuit.

3. (Original) The method according to claim 2, wherein the semiconductor film is formed on the surface of the porous layer after forming a protective film on inner walls of pores in the porous layer.

4. (Original) The method according to claim 1, wherein the member is obtained by forming the semiconductor element and/or semiconductor integrated circuit on a surface of a semiconductor substrate and implanting ions from the surface side to a predetermined depth to form the separation layer.

5. (Original) The method according to claim 2, wherein the semiconductor substrate is a single-crystal silicon substrate or a compound semiconductor substrate.

6. (Original) The method according to claim 4, wherein the semiconductor substrate is a single-crystal silicon substrate or a compound semiconductor substrate.

7. (Cancelled)

8. (Currently Amended) The method according to claim 1, wherein after the separation step, ~~the separation layer remaining on the semiconductor film side is removed, and then,~~ the chip forming step is executed.

9. (Currently Amended) The method according to claim 1, wherein after ~~the separation step~~ and the chip forming step, the ~~step of removing the separation layer remaining on the semiconductor film side~~ step is executed.

10 to 13. (Cancelled)

14. (New) The method according to claim 1, wherein the separation step is executed by applying a pressure of a fluid to the separation layer.

15. (New) The method according to claim 1, wherein after the chip forming step, the separation step is executed.

16. (New) The method according to claim 1, wherein after the removing step, the chip forming step is executed.